

### 60V N-Channel MOSFET



TO-92

# **5**

### Pin Definition:

- 1. Source
- 2. Gate
- 3. Drain

### **PRODUCT SUMMARY**

V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (mA)
60	5 @ V <sub>GS</sub> = 10V	100
	5.5 @ V <sub>GS</sub> = 5V	100

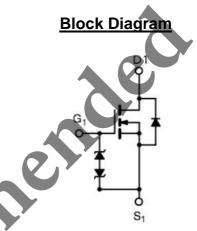
### **Features**

- Low On-Resistance
- ESD Protection
- High Speed Switching
- Low Voltage Drive

### **Ordering Information**

Part No.	Package	Packing
TSM2N7000KCT B0G	TO-92	1Kpcs / Bulk
TSM2N7000KCT A3G	TO-92	2Kpcs / Ammo

Note: "G" denotes for Halogen Free



N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		V <sub>DS</sub>	60	V	
Gate-Source Voltage		$V_{GS}$	±20	V	
Drain Current	Continuous @ T <sub>A</sub> =25°C	I <sub>D</sub>	300	mA	
	Pulsed	I <sub>DM</sub>	700		
Drain Reverse Current	Continuous @ T <sub>A</sub> =25°C	I <sub>DR</sub>	300	mA	
	Pulsed	I <sub>DMR</sub>	700		
Maximum Power Dissipation		P <sub>D</sub>	400	mW	
Operating Junction Temperature		$T_J$	+150	°C	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

### **Thermal Performance**

Parameter	Symbol	Limit	Unit
Lead Temperature (1/8" from case)	$T_L$	10	S
Junction to Ambient Thermal Resistance (PCB mounted)	RΘ <sub>JA</sub>	357	°C/W

### Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board,  $t \le 5$  sec.



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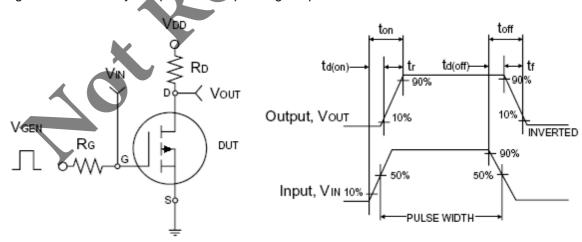


**Electrical Specifications** (Ta = 25°C, unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 10\mu A$	BV <sub>DSS</sub>	60			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V <sub>GS(TH)</sub>	1.0		2.5	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±10	uA
Zero Gate Voltage Drain Current	$V_{DS} = 60V, V_{GS} = 0V$	I <sub>DSS</sub>			1.0	uA
Desir Course On Otata Basistanaa	$V_{GS} = 10V, I_D = 100mA$			3	5	
Drain-Source On-State Resistance	$V_{GS} = 5V, I_D = 100mA$	$R_{DS(ON)}$		3.6	5.5	Ω
Forward Transconductance	$V_{DS} = 10V, I_{D} = 200mA$	g <sub>fs</sub>	100			mS
Diode Forward Voltage	$I_S = 300 \text{mA}, V_{GS} = 0 \text{V}$	V <sub>SD</sub>	(	0.9	1.2	V
Dynamic <sup>b</sup>						
Total Gate Charge	$V_{DS} = 10V, I_{D} = 250mA,$ $V_{GS} = 4.5V$	Q <sub>g</sub>		0.4		nC
Input Capacitance	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V,	C <sub>iss</sub>		7.32		
Output Capacitance		Coss		3.42		pF
Reverse Transfer Capacitance	f = 1.0MHz	C <sub>rss</sub>		7.63		
Switching <sup>c</sup>						
Turn-On Delay Time	$V_{DD} = 30V, R_G = 10\Omega$	t <sub>d(on)</sub>		25		0
Turn-Off Delay Time	$I_D = 100 \text{mA}, V_{GEN} = 10 \text{V},$	t <sub>d(off)</sub>		35		nS

### Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2% b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

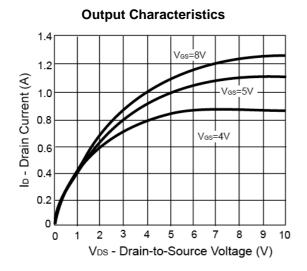
Switchin Waveforms

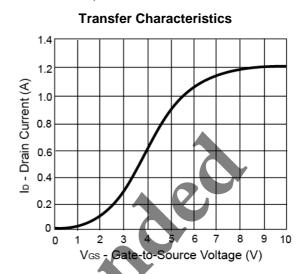


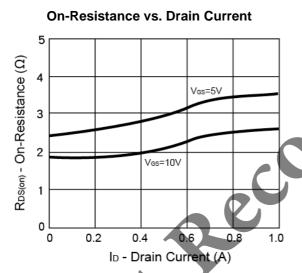
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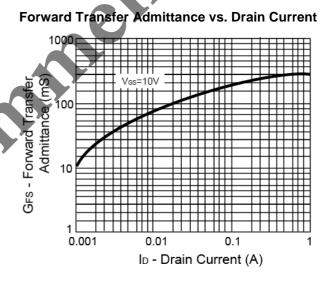


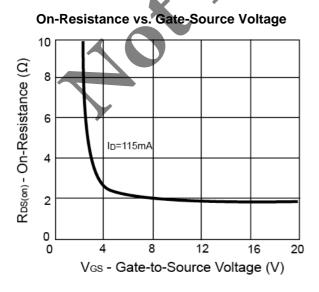
### **Electrical Characteristics Curve** (Ta = 25°C, unless otherwise noted)

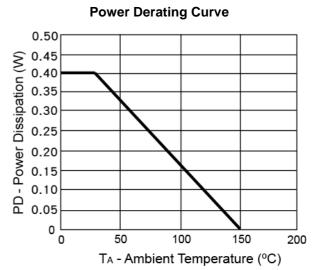










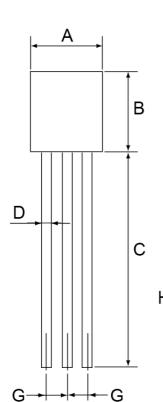




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# **TO-92 Mechanical Drawing**



TO-92 DIMENSION					
DIM	MILLIMETERS		INCHES		
DIIVI	MIN	MAX 🔺	MIN	MAX	
Α	4.30	4.70	0.169	0.185	
В	4.30	4.70	0.169	0.185	
С	13.53	(typ)	0.532 (typ)		
D	0.39	0.49	0.015	0.019	
Е	1.18	1.28	0.046	0.050	
F	3.30	3.70	0.130	0.146	
G	1.27	1.31	0.050	0.051	
Н	0.33	0.43	0.013	0.017	





Y = Year Code

**M** = Month Code for Halogen Free Product

 $\mathbf{O}$  =Jan  $\mathbf{P}$  =Feb  $\mathbf{Q}$  =Mar  $\mathbf{R}$  =Apr

S =May T =Jun U =Jul V =Aug

W =Sep X =Oct Y =Nov Z =Dec

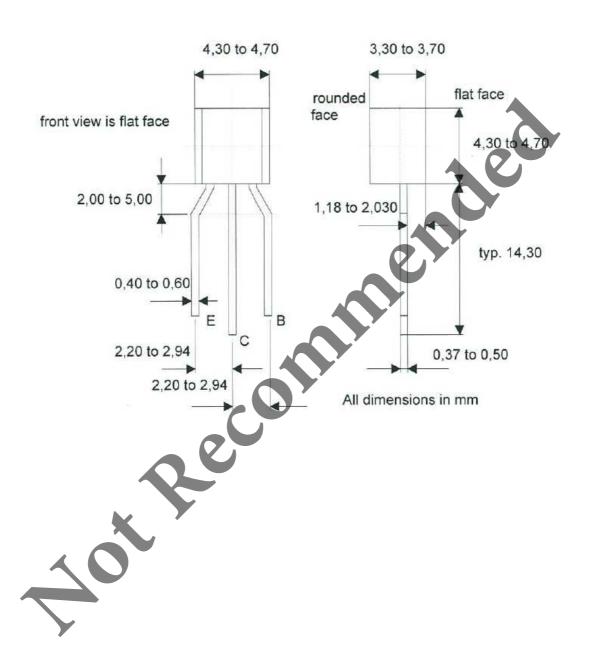
L = Lot Code



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# **TO-92 Ammo Pack Mechanical Drawing**









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